

# High Voltage Standard Rectifier Module

$V_{RRM}$  = 2x2800 V

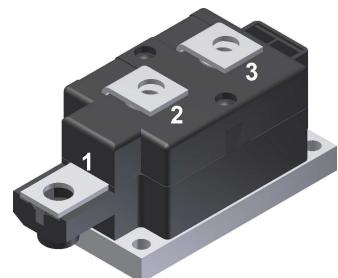
$I_{FAV}$  = 240 A

$V_F$  = 1.01 V

## Phase leg

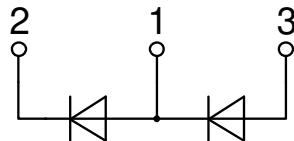
### Part number

**MDD175-28N1**



Backside: isolated

 E72873



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling

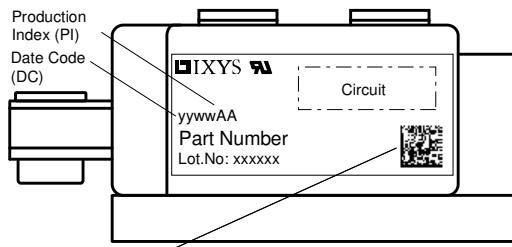
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**Rectifier**

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			2900	V
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			2800	V
$I_R$	reverse current	$V_R = 2800 \text{ V}$ $V_R = 2800 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$		1 5	mA
$V_F$	forward voltage drop	$I_F = 200 \text{ A}$ $I_F = 400 \text{ A}$ $I_F = 200 \text{ A}$ $I_F = 400 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.07 1.26 1.01 1.26	V
$I_{FAV}$	average forward current	$T_C = 100^\circ\text{C}$ $180^\circ \text{ sine}$ $d = 0.5$	$T_{VJ} = 150^\circ\text{C}$		240	A
$V_{F0}$ $r_F$	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.74 1.27	V mΩ
$R_{thJC}$	thermal resistance junction to case				0.14	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.04		K/W
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		900	W
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = 0 \text{ V}$		8.50 9.18 7.23 7.81	kA
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = 0 \text{ V}$		361.3 350.6 261.0 253.4	kA²s
$C_J$	junction capacitance	$V_R = 1100 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$	182		pF

Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				680		g
$M_D$	mounting torque		4.5		7	Nm
$M_T$	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air		terminal to terminal		16.0	mm
$d_{Spb/Apb}$			terminal to backside		16.0	mm
$V_{ISOL}$	isolation voltage	t = 1 second t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		4800 4000	V V



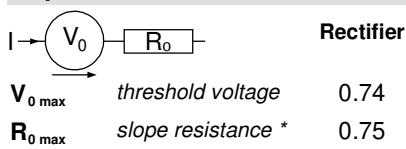
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

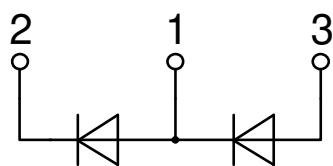
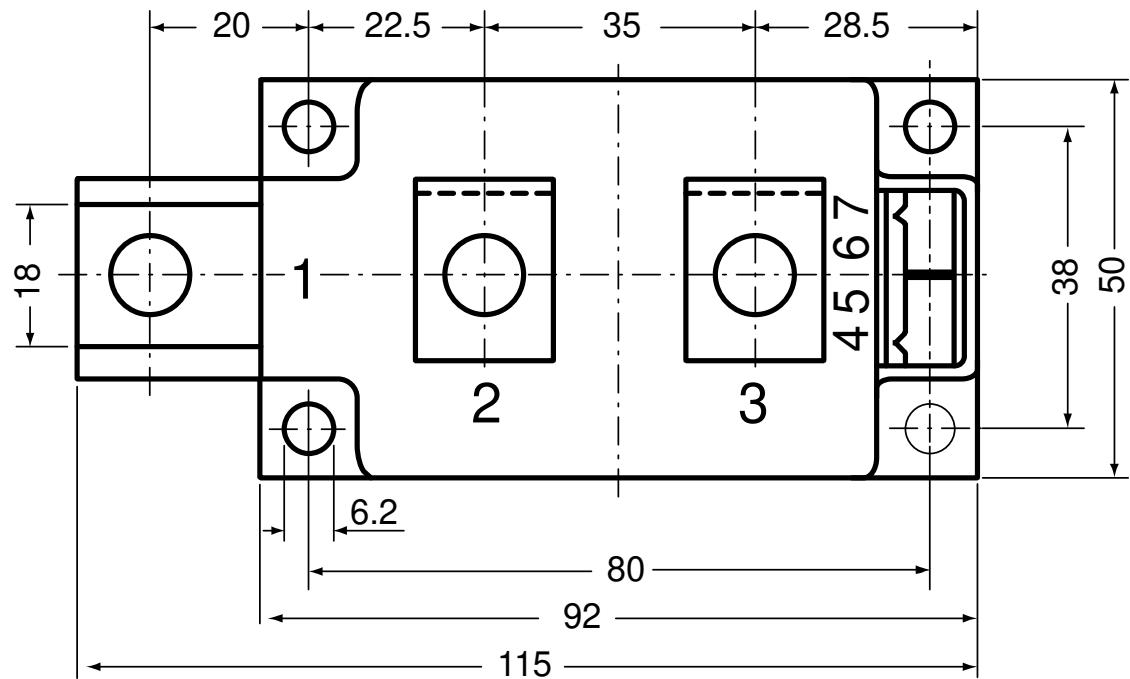
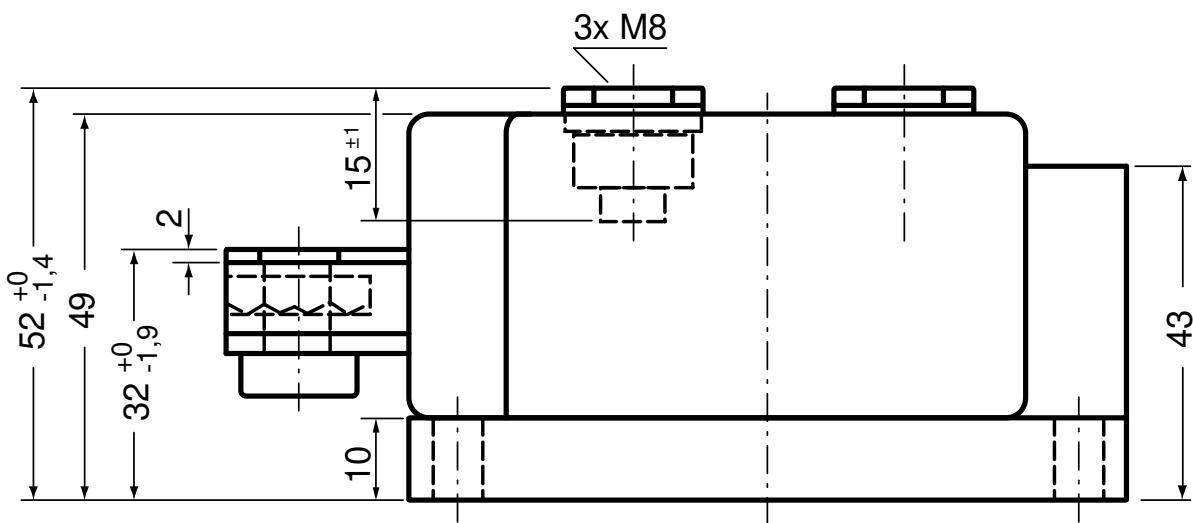
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD175-28N1	MDD175-28N1	Box	3	504295

### Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 150^\circ\text{C}$



**Outlines Y1**


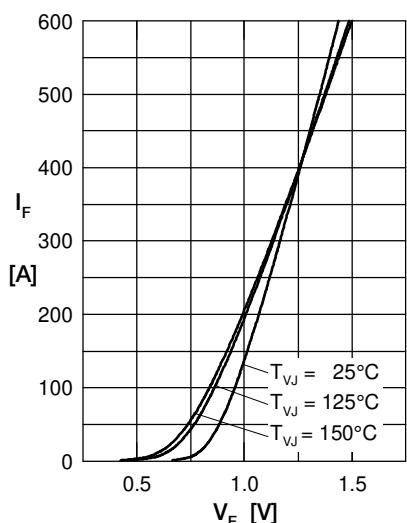
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

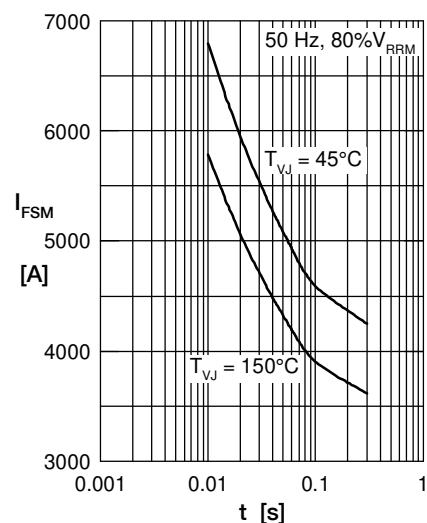


Fig. 2 Surge overload current

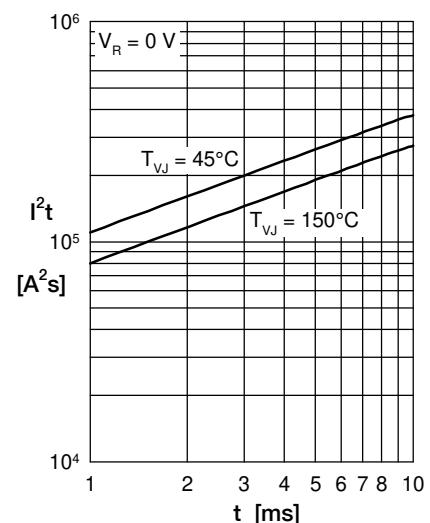


Fig. 3  $I^2t$  versus time per diode

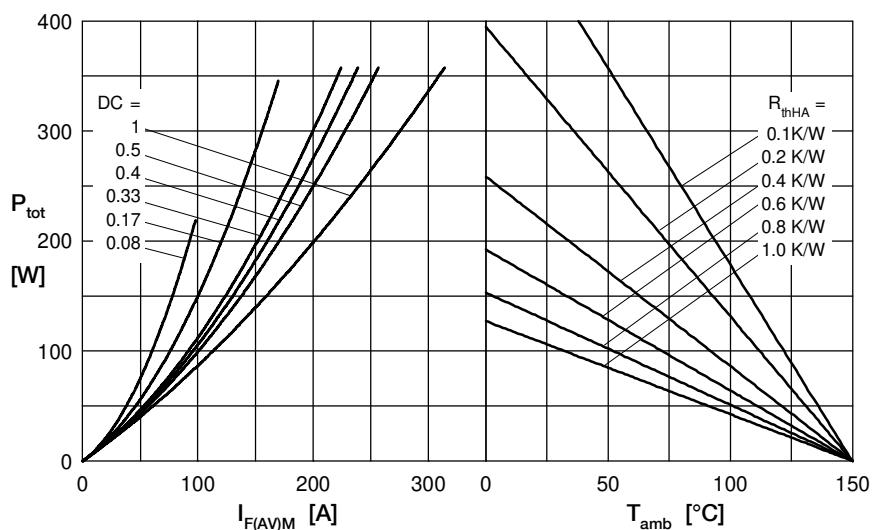


Fig. 4 Power dissipation vs. direct output current and ambient temperature

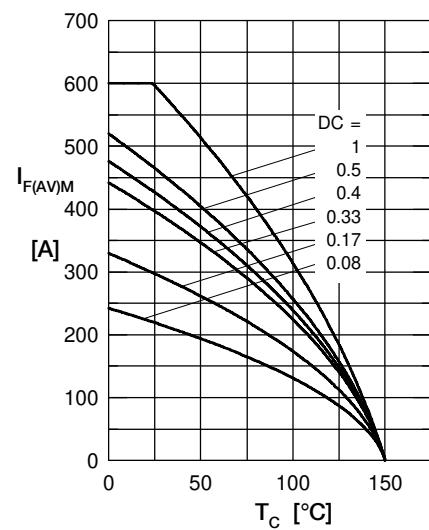


Fig. 5 Max. forward current vs. case temperature

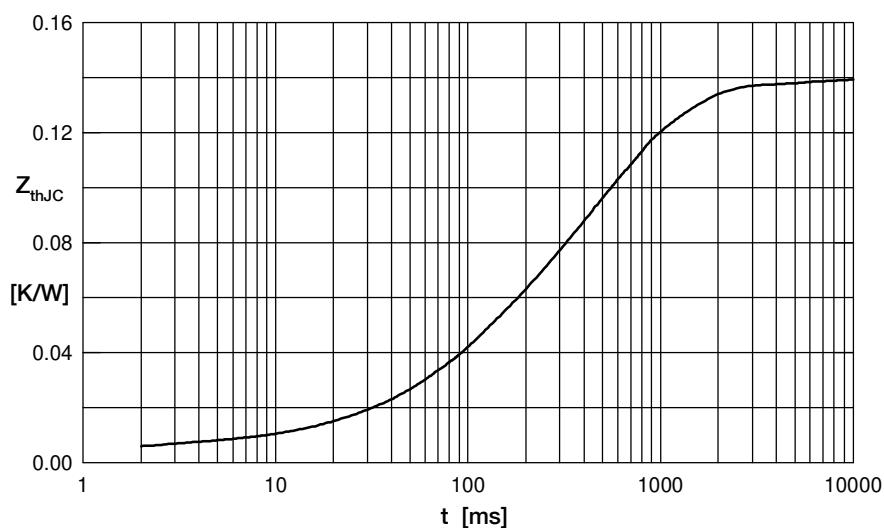


Fig. 6 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	0.8
5	0.00001	0.00001